

REMARKS

The Official Action mailed June 4, 2002 has been received and its contents carefully noted. Filed concurrently herewith is a *Request for Two Month Extension of Time*, which extends the shortened statutory period for response to November 4, 2002. Accordingly, Applicant respectfully submits that this response is being timely filed.

It is noted that Applicants have apparently not received acknowledgement of any of the Information Disclosure Statements filed in the subject application, including those filed on January 25, 1999; April 13, 2000; July 25, 2000; November 8, 2000; March 7, 2001; March 28, 2001; March 13, 2002; May 24, 2002; and September 25, 2002. Applicants respectfully request that the Examiner provide an initialed copy of the Form PTO-1449 evidencing consideration of these Information Disclosure Statements with the next communication.

Claims 1-22 are pending in the present application, of which claims 1, 4, 7, 10, 12, 15, 18, and 20 are independent. Dependent claims 3, 6, 9, 13, 16, and 19 are amended herewith to correct typographical errors in the thickness ranges recited therein. For the reasons set forth in detail below, all claims are believed to be in condition for allowance and favorable reconsideration is requested.

The Official Action appears to maintain the rejection of all claims 1-22 as anticipated or obvious based on U.S. Patent 5,424,230 to Wakai. Applicant has previously submitted verified English translations of Japanese priority application numbers 4-124324 and 4-113027 to overcome these rejections.

The Official Action first acknowledges that Applicant has submitted translations of Japanese priority application numbers 4-124324 and 4-113027 and notes that no translation of JP 4-102202 has been submitted. As applicant does not now believe that the disclosure of JP 4-102202 is necessary to support the presently pending claims, no translation of JP 4-102202 is believed to be required or necessary. It is understood that the Official Action is merely confirming that applicant cannot now rely on JP 4-102202 since no translation is submitted and that the Official Action is not alleging that such translation is required in order to perfect applicant's priority claim based on Japanese priority application numbers 4-124324 and 4-113027. If this understanding is not correct, clarification is requested.

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The Official Action next asserts that the declaration must have a parent application identified in order to obtain the earlier priority date. Thus, it is understood that the Official Action alleges that applicant's priority claim to Japanese priority application numbers 4-124324 and 4-113027 is improper without reference to an earlier parent application in the declaration.

Applicant respectfully disagrees and asserts that the declaration of the subject application is sufficient and in accord with established rules to maintain priority to Japanese priority application numbers 4-124324 and 4-113027. The present application was filed January 25, 1999. As filed, the application claimed priority to U.S. Application Serial numbers 08/841,638 and 08/460,560. U.S. Application Serial number 08/460,560 claimed priority to U.S. Application Serial number 08/037,162, but the '162 application was inadvertently omitted from the Preliminary Amendment filed with the subject application on January 25, 1999. Thus, in an amendment filed November 15, 2001, the subject application was amended to include specific reference to the '162 application as required by 35 U.S.C. 120. The subject application was filed with a copy of the declaration from U.S. Application Serial number 08/037,162 in accord with the provisions of 37 CFR 1.63(d). It is respectfully submitted that the declaration is in conformance with all requirements as set forth in Rule 63(d) and favorable reconsideration is requested in view thereof.

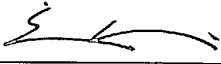
Paragraph 2 of the Official Action asserts that the translations of the foreign priority documents do not contain information pertaining to hydrogen doping nor a hydrogen containing layer and thus fail to support claims 2, 5, 7-9, 11 and 12-14. It is respectfully submitted that JP 4-113027, in particular, appears to teach that (1) a silicon nitride layer can contain hydrogen and oxygen as taught in paragraph [0008], and (2) the semiconductor layer is added with hydrogen for reducing dangling bonds as taught in paragraph [0016] or [0023], or as taught in paragraph [0029]. Therefore, it is respectfully submitted that the limitations of claims 2, 5, 7-9, 11, and 12-14 are fully supported by the priority documents and favorable reconsideration is requested.

In view of the above, it is respectfully submitted that the claims of the subject application are entitled to the filing date of the Japanese priority applications and that all remaining rejections are overcome thereby. Favorable reconsideration is requested.

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Should the Examiner believe that anything further would be desirable to place this application in better condition for allowance, the Examiner is invited to contact Applicant's undersigned attorney at the telephone number listed below.

Respectfully submitted,



Eric J. Robinson
Reg. No. 38,285

Robinson Intellectual Property Law Office, P.C.
PMB 955
21010 Southbank Street
Potomac Falls, Virginia 20165
(571) 434-6789

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VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS:

Please amend claims 3, 6, 9, 13, 16 and 19 as follows:

3. (Amended) A semiconductor device according to claim 1 wherein a thickness of said first insulating film is 10-50 nm, a thickness of said second insulating film is [10-800] 100-800 nm, a thickness of said third insulating film is 50-200 nm and a thickness of said fourth insulating film is 2-20 nm.

6. (Amended) A semiconductor device according to claim 4 wherein a thickness of said first insulating film is 10-50 nm, a thickness of said second insulating film is [10-800] 100-800 nm, a thickness of said third insulating film is 50-200 nm and a thickness of said fourth insulating film is 2-20 nm.

9. (Amended) A semiconductor device according to claim 7 wherein a thickness of said first insulating film is 10-50 nm, a thickness of said second insulating film is [10-800] 100-800 nm, a thickness of said third insulating film is 50-200 nm and a thickness of said fourth insulating film is [2-10] 2-20 nm.

13. (Amended) A semiconductor device according to claim 12 wherein a thickness of said first insulating film is 10-50 nm, a thickness of said second insulating film is [10-800] 100-800 nm, a thickness of said third insulating film is 50-200 nm and a thickness of said fourth insulating film is 2-20 nm.

16. (Amended) A semiconductor device according to claim 15 wherein a thickness of said first insulating film is 10-50 nm, a thickness of said second insulating film is [10-800] 100-800 nm, a thickness of said third insulating film is 50-200 nm and a thickness of said fourth insulating film is 2-20 nm.

19. (Amended) A semiconductor device according to claim 18 wherein a thickness of said first insulating film is 10-50 nm, a thickness of said second insulating

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film is [10-800] 100-800 nm, a thickness of said third insulating film is 50-200 nm and a thickness of said fourth insulating film is 2-20 nm.

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